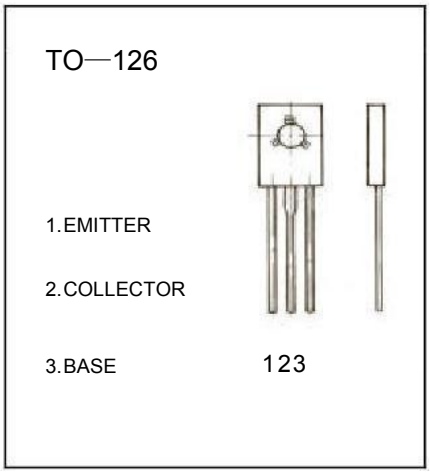
TO-126 Plastic-Encapsulate Transistors

BD235 TRANSISTOR（ NPN ）



FEATURES

Power dissipation

P_{CM}: 1.25 W（Tamb=25℃）

Collector current

I_{CM}: 2 A

Collector-base voltage

$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=1mA , I_E=0	60			V
Collector-emitter sustaining voltage	$V_{CEO(SUS)}$	I_C=10mA , I_B=0	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=60V, I_E=0			100	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0			1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=2V, I_C=150mA	40			
DC current gain	$h_{FE(2)}$	V_{CE}=2V, I_C=1A	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=1A, I_B=100mA			0.6	V
Transition frequency	f_T	V_{CE}=10V, I_C=250mA f=10MHz	3			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	1	2	3
Range	40-100	63-160	100-250